

## Silicon PNP Power Transistors

2SA1120

## DESCRIPTION

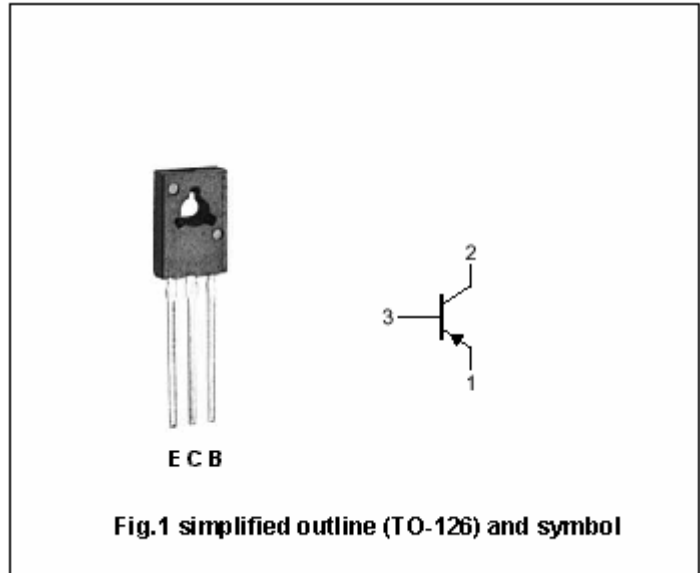
- With TO-126 package
- High transition frequency
- Low collector saturation voltage

## APPLICATIONS

- Audio power amplifier applications

## PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

Absolute maximum ratings( $T_a=25^\circ$ )

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	-35	V
$V_{CEO}$	Collector-emitter voltage	Open base	-35	V
$V_{EBO}$	Emitter-base voltage	Open collector	-6	V
$I_C$	Collector current		-5	A
$I_B$	Base current		-1	A
$P_D$	Total power dissipation	$T_a=25^\circ$	1.5	W
		$T_C=25^\circ$	5	
$T_j$	Junction temperature		150	$^\circ$
$T_{stg}$	Storage temperature		-55 $^\circ$ +150	$^\circ$

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## CHARACTERISTICS

T<sub>j</sub>=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =-10mA ; I <sub>B</sub> =0	-35			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =-4A ; I <sub>B</sub> =-0.1A			-1.0	V
V <sub>BE</sub>	Base-emitter on voltage	I <sub>C</sub> =-4A ; V <sub>CE</sub> =-2V			-1.5	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =-35V ; I <sub>E</sub> =0			-0.1	mA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =-6V ; I <sub>C</sub> =0			-0.1	mA
h <sub>FE-1</sub>	DC current gain	I <sub>C</sub> =-500mA ; V <sub>CE</sub> =-2V	200			
h <sub>FE-2</sub>	DC current gain	I <sub>C</sub> =-4A ; V <sub>CE</sub> =-2V	70			
C <sub>ob</sub>	Output capacitance	I <sub>E</sub> =0 ; V <sub>CB</sub> =-10V f=1MHz		62		pF
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =-500mA ; V <sub>CE</sub> =-2V		170		MHz

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PACKAGE OUTLINE

